ABSTRACT OF THE DISCLOSURE

The present invention is directed to improve high frequency characteristics by reducing inductance of a source. In an HEMT assembled in a power amplifier device, each of a drain electrode, a source electrode, and a gate electrode is constructed by a base portion and a plurality of fingers projected in a comb-teeth shape from the base portion, and the fingers of the electrodes mesh with each other. In the source electrode, a width of the fingers positioned at both ends of the plurality of fingers is wider than a width of each of the fingers positioned between both ends. The width of each of the fingers positioned at both ends is a width equal to or larger than a sum of the widths of the plurality of fingers positioned between both ends, and the width of the base portion is wider than that of each of the fingers positioned at both ends. An electrode pad provided for the source base portion and an external electrode terminal are connected to each other via a conductive wire.